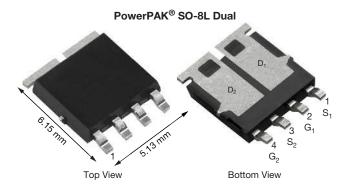
### SQJ968EP



**Vishay Siliconix** 

# Automotive Dual N-Channel 60 V (D-S) 175 °C MOSFET

| PRODUCT SUMMARY                           |                |
|---|----------------|
| V <sub>DS</sub> (V)                       | 60             |
| $R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$  | 0.0336         |
| $R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$ | 0.0444         |
| I <sub>D</sub> (A) per leg                | 23.5           |
| Configuration                             | Dual           |
| Package                                   | PowerPAK SO-8L |

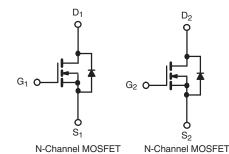


### **FEATURES**

- TrenchFET<sup>®</sup> power MOSFET
- AEC-Q101 qualified
- 100 %  $R_q$  and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



RoHS COMPLIANT HALOGEN FREE



| ABSOLUTE MAXIMUM RATING                                   | <b>S</b> (T <sub>C</sub> = 25 °C, unles | s otherwise noted | )     |      |
|---|---|-------------------|-------|------|
| PARAMETER   |   | SYMBOL            | LIMIT | UNIT |
| Drain-Source Voltage                                      |   | V <sub>DS</sub>   | 60    | v    |
| Gate-Source Voltage                                       |   | V <sub>GS</sub>   | ± 20  | v    |
| Continuous Drain Current <sup>a</sup>                     | T <sub>C</sub> = 25 °C                  | 1                 | 23.5  |      |
|   | T <sub>C</sub> = 125 °C                 | I <sub>D</sub>    | 13.5  |      |
| Continuous Source Current (Diode Conduction) <sup>a</sup> |   | I <sub>S</sub>    | 23    | А    |
| Pulsed Drain Current <sup>b</sup>                         | I <sub>DM</sub>                         | 72                |       |      |
| Single Pulse Avalanche Current                            | L = 0.1 mH                              | I <sub>AS</sub>   | 9     |      |
| Single Pulse Avalanche Energy                             |   | E <sub>AS</sub>   | 4     | mJ   |
| Maria a Dana Diasia ta ta b                               | T <sub>C</sub> = 25 °C                  | Р                 | 42    | w    |
| Maximum Power Dissipation <sup>b</sup>                    | $T_{\rm C} = 125 ^{\circ}{\rm C}$       | P <sub>D</sub>    | 14    | vv   |
| Operating Junction and Storage Temperature                | T <sub>J</sub> , T <sub>stg</sub>       | -55 to +175       | °C    |      |
| Soldering Recommendations (Peak Tempera                   | ature) <sup>d, e</sup>                  |                   | 260   |      |

| THERMAL RESISTANCE RATINGS |                        |                   |       |      |
|----------------------------|------------------------|-------------------|-------|------|
| PARAMETER                  |                        | SYMBOL            | LIMIT | UNIT |
| Junction-to-Ambient        | PCB Mount <sup>c</sup> | R <sub>thJA</sub> | 85    | °C/W |
| Junction-to-Case (Drain)   |                        | R <sub>thJC</sub> | 3.5   | C/W  |

Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR4 material).

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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# SQJ968EP

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| PARAMETER                             | SYMBOL                   | TES   | MIN.   | TYP. | MAX.                        | UNIT   |    |
|---------------------------------------|--------------------------|---|--|------|-----------------------------|--------|----|
| Static                                |                          |   |  |      | •                           |        |    |
| Drain-Source Breakdown Voltage        | V <sub>DS</sub>          | V <sub>GS</sub> =   | $V_{GS} = 0 V, I_{D} = 250 \mu A$                      |      | -                           | -      | V  |
| Gate-Source Threshold Voltage         | V <sub>GS(th)</sub>      | V <sub>DS</sub> =   | = V <sub>GS</sub> , I <sub>D</sub> = 250 μΑ            | 1.5  | 2.0                         | 2.5    | v  |
| Gate-Source Leakage                   | I <sub>GSS</sub>         | V <sub>DS</sub> =   | : 0 V, V <sub>GS</sub> = ± 20 V                        | -    | -                           | ± 100  | nA |
|                                       |                          | $V_{GS} = 0 V$  | V <sub>DS</sub> = 60 V                                 | -    | -                           | 1      |    |
| Zero Gate Voltage Drain Current       | I <sub>DSS</sub>         | $V_{GS} = 0 V$  | V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C        | -    | V<br>2.0 2.5 V<br>- ±100 nA |        |    |
|                                       |                          | $V_{GS} = 0 V$  | V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C        | -    | -                           | 150    |    |
| On-State Drain Current <sup>a</sup>   | I <sub>D(on)</sub>       | $V_{GS} = 10 V$   | $V_{DS} \ge 5 V$                                       | 30   | -                           | -      | Α  |
|                                       |                          | $V_{GS} = 10 V$   | I <sub>D</sub> = 4.8 A                                 | -    | 0.0280                      | 0.0336 |    |
| Durin Source On State Desistance a    | Б                        | $V_{GS} = 10 V$   | I <sub>D</sub> = 4.8 A, T <sub>J</sub> = 125 °C        | -    | -                           | 0.0900 |    |
| Drain-Source On-State Resistance a    | R <sub>DS(on)</sub>      | V <sub>GS</sub> = 10 V  | I <sub>D</sub> = 4.8 A, T <sub>J</sub> = 175 °C        | -    | -                           | 0.1430 | Ω  |
|                                       |                          | $V_{GS} = 4.5 V$  | I <sub>D</sub> = 4.2 A                                 | -    | 0.0370                      | 0.0444 |    |
| Forward Transconductance <sup>b</sup> | <b>g</b> <sub>fs</sub>   | V <sub>DS</sub> = 15 V, I <sub>D</sub> = 4.8 A  |  | -    | 16                          | -      | S  |
| Dynamic <sup>b</sup>                  |                          | •   |  | •    |                             | •      |    |
| Input Capacitance                     | C <sub>iss</sub>         |   | V <sub>DS</sub> = 30 V, f = 1 MHz                      | -    | 571                         | 714    | pF |
| Output Capacitance                    | C <sub>oss</sub>         | $V_{GS} = 0 V$  |  | -    | 98                          | 123    |    |
| Reverse Transfer Capacitance          | C <sub>rss</sub>         |   |  | -    | 38                          | 48     |    |
| Total Gate Charge <sup>c</sup>        | Qg                       |   |  | -    | 12.3                        | 18.5   |    |
| Gate-Source Charge <sup>c</sup>       | Q <sub>gs</sub>          | $V_{GS} = 10 V$   | $V_{DS} = 30 \text{ V}, \text{ I}_{D} = 4.5 \text{ A}$ | -    | 1.9                         | -      | nC |
| Gate-Drain Charge <sup>c</sup>        | Q <sub>gd</sub>          |   |  | -    | 2.6                         | -      |    |
| Gate Resistance                       | R <sub>g</sub>           | f = 1 MHz   |  | 1.3  | -                           | 6      | Ω  |
| Turn-On Delay Time <sup>c</sup>       | t <sub>d(on)</sub>       |   |  | -    | 8                           | 12     |    |
| Rise Time <sup>c</sup>                | t <sub>r</sub>           | $\label{eq:VDD} \begin{array}{l} V_{DD} = 30 \; V, \; R_L = 30 \; \Omega \\ I_D \cong 1 \; A, \; V_GEN = 10 \; V, \; R_g = 1 \; \Omega \end{array}$ |  | -    | 9                           | 13.5   | ns |
| Turn-Off Delay Time <sup>c</sup>      | t <sub>d(off)</sub>      |   |  | -    | 19.5                        | 29     |    |
| Fall Time <sup>c</sup>                | t <sub>f</sub>           |   | -  | 6.5  | 10                          |        |    |
| Source-Drain Diode Ratings and Chara  | acteristics <sup>b</sup> | ·   |  |      | •                           |        |    |
| Pulsed Current <sup>a</sup>           | I <sub>SM</sub>          |   |  | -    | -                           | 32     | Α  |
| Forward Voltage                       | V <sub>SD</sub>          | I <sub>F</sub> = 3.1 A, V <sub>GS</sub> = 0 V   |  | -    | 0.8                         | 1.1    | V  |

Notes

a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

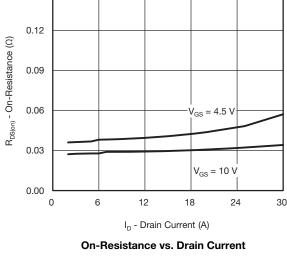
c. Independent of operating temperature.

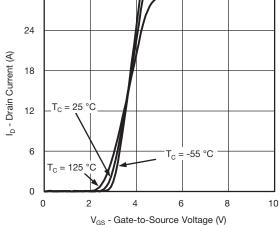
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

T<sub>C</sub> = 125 °C T<sub>C</sub> -55 °C 0 3 4 5 0 1 2 1 2 V<sub>GS</sub> - Gate-to-Source Voltage (V) **Transfer Characteristics** 1000

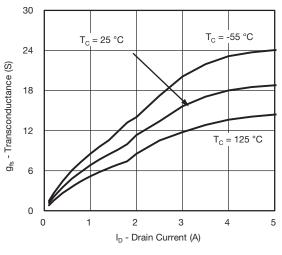
#### $V_{GS} = 3 V$ 0 8 10 6 0 2 V<sub>DS</sub> - Drain-to-Source Voltage (V) **Output Characteristics** 30

30

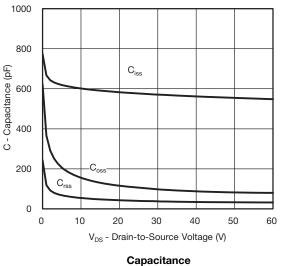












S16-1227-Rev. C, 20-Jun-16

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For technical questions, contact: automostechsupport@vishay.com





V<sub>GS</sub> = 10 V thru 5 V

 $V_{GS} = 4 V$ 

4

°C  $\Gamma_{\rm C} = 25$ 

24

18

12

6

0

10.0

8.0

6.0

4.0

2.0

0.0

0.15

0

l<sub>D</sub> - Drain Current (A)

0

2

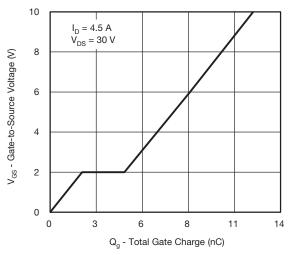
I<sub>D</sub> - Drain Current (A)

TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted) 30

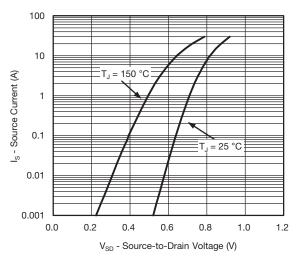
SQJ968EP



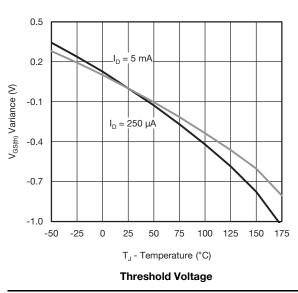
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

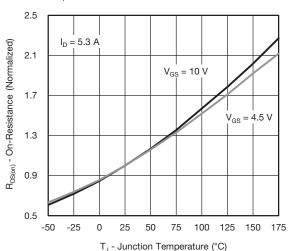




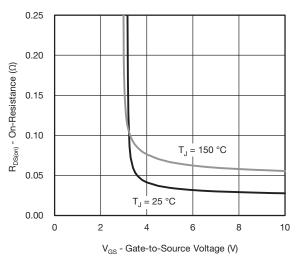


Source Drain Diode Forward Voltage

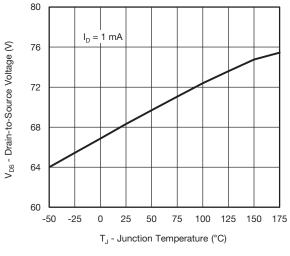




**On-Resistance vs. Junction Temperature** 



**On-Resistance vs. Gate-to-Source Voltage** 



Drain Source Breakdown vs. Junction Temperature

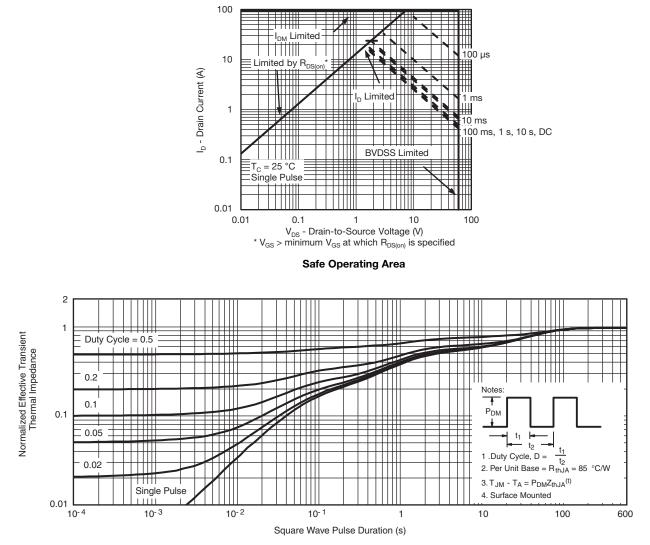
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### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



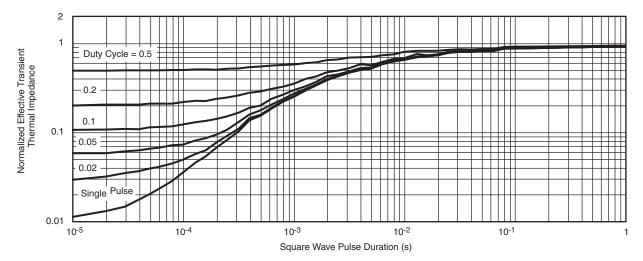
Normalized Thermal Transient Impedance, Junction-to-Ambient



## SQJ968EP

### Vishay Siliconix

### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?62817">www.vishay.com/ppg?62817</a>.



## SQJ968EP

Vishay Siliconix

#### **REVISION HISTORY**<sup>a</sup>

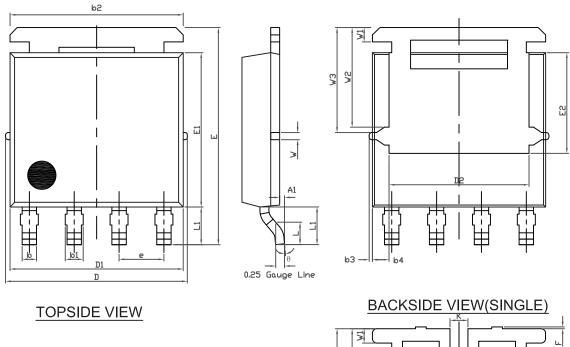
| <b>NEVISION</b> | moroni    |   |
|-----------------|-----------|---|
| REVISION        | DATE      | DESCRIPTION OF CHANGE                         |
| В               | 04-Aug-15 | Revised R <sub>g</sub> minimum limit          |
| С               | 14-Jun-16 | • I <sub>D</sub> and P <sub>D</sub> corrected |

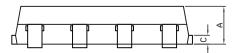
Note

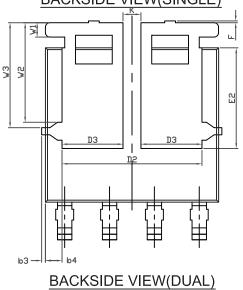
a. As of April 2014



# PowerPAK<sup>®</sup> SO-8L Case Outline 2







## **Package Information**



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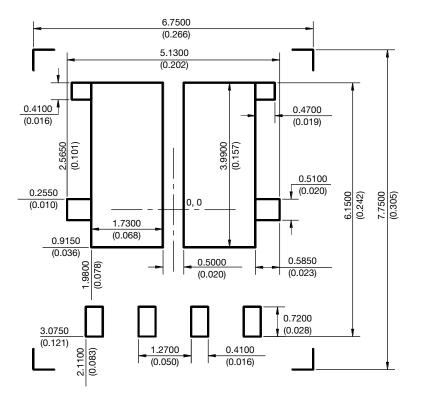
| DIM.  |                | MILLIMETERS |       |               | INCHES |       |  |
|-------|----------------|-------------|-------|---------------|--------|-------|--|
| DINI. | MIN. NOM. MAX. |             |       | MIN. NOM. MAX |        |       |  |
| А     | 1.00           | 1.07        | 1.14  | 0.039         | 0.042  | 0.045 |  |
| A1    | 0.00           | -           | 0.127 | 0.00          | -      | 0.005 |  |
| b     | 0.33           | 0.41        | 0.48  | 0.013         | 0.016  | 0.019 |  |
| b1    | 0.44           | 0.51        | 0.58  | 0.017         | 0.020  | 0.023 |  |
| b2    | 4.80           | 4.90        | 5.00  | 0.189         | 0.193  | 0.197 |  |
| b3    |                | 0.094       | •     |               | 0.004  |       |  |
| b4    |                | 0.47        |       |               | 0.019  |       |  |
| С     | 0.20           | 0.25        | 0.30  | 0.008         | 0.010  | 0.012 |  |
| D     | 5.00           | 5.13        | 5.25  | 0.197         | 0.202  | 0.207 |  |
| D1    | 4.80           | 4.90        | 5.00  | 0.189         | 0.193  | 0.197 |  |
| D2    | 3.86           | 3.96        | 4.06  | 0.152         | 0.156  | 0.160 |  |
| D3    | 1.63           | 1.73        | 1.83  | 0.064         | 0.068  | 0.072 |  |
| е     |                | 1.27 BSC    | •     | 0.050 BSC     |        |       |  |
| E     | 6.05           | 6.15        | 6.25  | 0.238         | 0.242  | 0.246 |  |
| E1    | 4.27           | 4.37        | 4.47  | 0.168         | 0.172  | 0.176 |  |
| E2    | 2.75           | 2.85        | 2.95  | 0.108         | 0.112  | 0.116 |  |
| F     | -              | -           | 0.15  | -             | -      | 0.006 |  |
| L     | 0.62           | 0.72        | 0.82  | 0.024         | 0.028  | 0.032 |  |
| L1    | 0.92           | 1.07        | 1.22  | 0.036         | 0.042  | 0.048 |  |
| К     |                | 0.51        |       |               | 0.020  |       |  |
| W     |                | 0.23        |       |               | 0.009  |       |  |
| W1    | 0.41           |             |       | 0.016         |        |       |  |
| W2    | 2.82           |             |       | 0.111         |        |       |  |
| W3    | 2.96           |             |       | 0.117         |        |       |  |
| q     | 0°             | -           | 10°   | 0°            | -      | 10°   |  |

Note

• Millimeters will gover



#### **RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L DUAL**



Recommended Minimum Pads Dimensions in mm (inches) Keep-out 6.75 (0.266) x 7.75 (0.305)

Revision: 07-Feb-12



Vishay

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